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Substitute for form 1449A/1450 INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Application Number		10/688,559	
				Filing Date		10/16/2003	
				First Named Inventor:		Christophe Pierrat	
				Examiner: A. Thompson <i>PAUL DINH</i>		GROUP: 2825	
Sheet	1	of	1	Attorney Docket Number		NTI-019-5-1D	
U.S. PATENT DOCUMENTS							
Examiner Initials*	Cited No. ¹	Document Number Number - Kind Code ^{2(f/known)}		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Figures Appear	
PD	A01	US-6,610,989	B1	08/26/2003	Takahashi		
	A02	US-6,370,441	B1	04/09/2002	Ohnuma		
	A03	US-6,145,118		11/07/2000	Tomita		
	A04	US-6,067,375		05/23/2000	Tsudaka		
	A05	US-6,058,203		05/02/2000	Tsudaka		
	A06	US-6,042,257		03/28/2000	Tsudaka		
	A07	US-5,885,748		03/23/1999	Ohnuma		
PD	A08	US-5,792,581		08/11/1998	Ohnuma		
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Examiner Initials*	Cite No. ¹	Foreign Patent Document Cntry Code ³ Number ⁴ Kind Code ^{5(f/known)}		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Figures Appear	T ⁶
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
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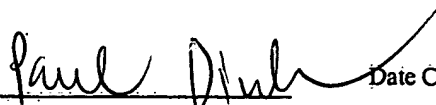
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INFORMATION DISCLOSURE CITATION PTO-1449		ATTY. DOCKET NO. NTI-019-5-1D		SERIAL NO. 10/688559 Filed Herewith		
		APPLICANT Pierrat, et al.				
		FILING DATE Filed Herewith 10/16/03		GROUP 2825		
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PD	4,231,811	11/4/80	Somekh, et al.	148	1.5	9/13/79
	4,456,371	6/26/84	Lin	355	71	6/30/82
	4,902,899	2/20/90	Lin, et al.	250	492.1	6/1/87
	5,498,579	3/12/96	Borodovsky, et al.	437	250	6/8/94
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	5,821,014	10/13/98	Chen, et al.	430	5	2/28/97
	5,862,058	1/19/99	Samuels, et al.	364	491	5/16/96
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	6,077,310	6/20/00	Yamamoto, et al.	716	19	1/29/99
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	5,958,635	9/28/1999	Reich, et al.	430	30	10/20/1997
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	6,007,310	12/28/1999	Jacobsen, et al.	417	362	5/23/1997
	6,114,071	9/5/2000	Chen, et al.	430	5	4/6/1998
	6,289,499	9/11/2001	Rieger, et al.	716	21	1/7/2000
PD	6,249,597 B1	6/19/2001	Tsudaka	382	144	12/17/1998

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U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
PD	6,014,456	1/11/2000	Tsudaka	382	144	7/15/1996
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PD	2002/0100004 A1	7/25/2002	Pierrat, et al.	716	5	3/15/2002

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<u>PD</u>	5,991,006	11/23/0199	Tsudaka	355	53	10/27/1997
	6,243,855 B1	6/5/2001	Kobayashi, et al.	716	19	9/29/1998

	5,663,893	09-1997	Wampler et al.	716	19
	6,416,907	07-2002	Winder et al.	430	5
	6,453,457	09-2002	Pierrat et al.	716	19
<u>PD</u>	6,523,162	02-2003	Agrawal et al.	716	19

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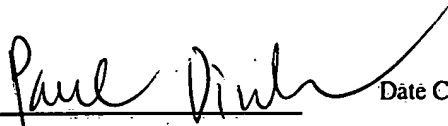
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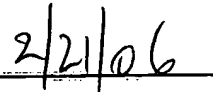
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PD	2,324,169 A	10/14/1998	GB			<input type="checkbox"/>	<input type="checkbox"/>
PD	WO 99/47981	9/23/1999	WU			<input type="checkbox"/>	<input type="checkbox"/>

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EXAMINER	Paul Dink	DATE CONSIDERED 2/21/06

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INFORMATION DISCLOSURE CITATION PTO-1449	ATTY. DOCKET NO. NTI-019-5-1D	SERIAL NO. 10/688559 Filed Herewith
	APPLICANT Pierrat, et al.	
	FILING DATE 10/16/03 Filed Herewith	GROUP 2825
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
PD	Saleh, B. et al., "Reduction Of Errors Of Microphotographic Reproductions By Optimal Corrections Of Original Masks", <i>Optical Engineering</i> , Vo. 20, No. 5, pp. 781-784, September/October 1981.	
PD	Spence, C. et al., "Integration Of Optical Proximity Correction Strategies In Strong Phase Shifters Design For Poly-Gate Layers", <i>Bacus News</i> , Vol. 15, Issue 12, pp. 1, 4-13, December 1999.	
EXAMINER Paul R. [Signature]	DATE CONSIDERED 2/21/06	

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INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No.	Serial No.
		NTI-019-5-1D	10/688559
		Applicant	Filed Herewith
		PIERRAT, Christophe	
		Filing Date	Group
		10/16/03	2825
		Filed Herewith	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
PD	Choi, Y., et al., "Optical Proximity Correction on Attenuated Phase Shifting Photo Mask for Dense Contact Array", LG Semicon Company (11 pages).		
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		Applicant PIERRAT, Christophe	Filing Date 10/16/03 Group 2825 Filed Herewith
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
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Paul Dink

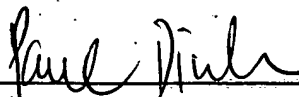
Date Considered:

2/21/06

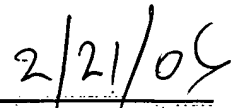
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		Applicant PIERRAT, Christophe	Filed Herewith
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
PD	Chuang, H., et al., "Practical Applications of 2-D Optical Proximity Corrections for Enhanced Performance of 0.25um Random Logic Devices", IEEE, pp. 18.7.1-18.7.4, December 1997.		

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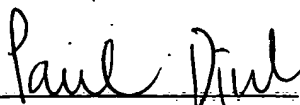
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	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
EXAMINER'S INITIALS	CITATION	
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